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Thermoelectric power in the quantum-Hall regime at very low temperatures

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Abstract

We have measured the thermoelectric power (TEP) of high mobility 2DEGs in the integer and fractional quantum Hall regime down to 100 mK. At low temperatures, fluctuation-like structures in the TEP are observed. Below 160 mK the TEP diverges around the filling factor \( \nu = \frac{1}{3} \) where the resistivity enters the insulating phase. The temperature dependence of the TEP at filling factors \( \nu = \frac{1}{2} \) and \( \frac{3}{4} \) resembles that of the zero field TEP enhanced by a constant factor. This is interpreted in terms of the phonon drag of composite fermions.

1. Introduction

The galvanomagnetic properties of two-dimensional electron gases (2DEGs) display a number of interesting phenomena such as the integer quantum-Hall-effect (IQHE) [1], the fractional quantum-Hall-effect (FQHE) [2], and the appearance of an insulating phase (IP) at low filling factors which has been attributed to a pinned Wigner solid [3].

Because the thermoelectric power (TEP) of 2DEGs in GaAs-Ga[sub x]Al[sub 1-x]As heterostructures is usually dominated by phonon drag, it provides a direct measure of the electron–phonon interaction [4, 5] and can therefore yield complementary information on the nature of the 2DEG compared to resistivity (which is determined by electron-impurity scattering). The recent review by Gallagher and Butcher [6] on the TEP of 2DEGs provides a good introduction to the present work. The relation between the applied temperature gradient (which supplies the driving force) \( \nabla T \) and the induced electric field \( E \) defines the TEP tensor \( S \): \( E = SVT \).

In this paper we will report the first experimental results concerning the \( S \) of a 2DEG at temperatures \( T \) down to 100 mK in high magnetic fields. We will show that with decreasing temperature additional structures in the TEP appear and, at the lowest temperatures, a diverging TEP is observed at filling factors where the IP in resistivity measurements shows up. Furthermore, we will present the temperature dependence of the TEP at \( \nu = \frac{1}{2} \) and \( \nu = \frac{3}{4} \) and compare it to the zero field TEP in the framework of the composite fermion model. We will mainly concentrate on \( S_{xx} \) but most statements also apply to \( S_{yx} \).

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2. Experimental

We investigated three high mobility (μ ≈ 200 m²/V s) GaAs-Ga₁₋₅₅Al₅₅As heterostructures (kindly supplied by Philips Research Laboratory, Redhill, England) labeled G645 (n = 0.75 x 10¹¹ cm⁻²), G647 (n = 0.43 x 10¹¹ cm⁻²), and G650 (n = 1.0 x 10¹¹ cm⁻²). Each 2DEG was grown on a semi-insulating GaAs substrate and was formed into a Hall bar with eight AuGeNi diffused ohmic contacts.

The experiments were carried out in the vacuum space of a ³He-⁴He dilution refrigerator adapted for use in high magnetic fields by having no metallic heat exchangers [7]. To avoid further eddy current heating, the sample holder was made of plastic and the only metal parts were in the thermal anchoring of the sample to the mixing chamber. The free-standing sample was In-soldered to the cold finger and the thermal gradient was produced by a heater glued to the free end. Typical temperature differences were a few tens of mK across the 2DEG and never exceeded 10% of the absolute temperature. Both VT and T were measured with two RuO₂ film resistors mounted on the rear side of the substrate. Special care was taken to eliminate all extraneous sources of heat loss from the sample.

As a check for the thermometry we have measured the thermal conductivity λ of the samples. λ is determined by the phonons in the three-dimensional substrate. Experimentally, λ follows the T³-dependence expected for a constant phonon mean free path which is limited by boundary scattering.

The TEP was measured using pulsed heating and detected at twice the frequency of the electrical heater current using a lock-in technique. The measuring frequencies were in the range 2–12 Hz. We verified the thermal response time being fast enough by obtaining the same results (within 10%) for different frequencies.

3. Results and discussion

Although at T > 400 mK the TEP is very much smaller in the IQH regime than in the FQH regime, the IQH TEP becomes comparable to, and even bigger than, the FQH TEP for T < 350 mK (see Fig. 1). At the lowest temperatures, the most pronounced structure is the peak between filling factors ν = 1 and ν = 2, i.e. between the two lowest spin-split Landau levels.

With decreasing T the TEP increasingly exhibits fluctuation-like structure. This is very reproducible for different field sweeps and is similar at different T, but the details of the structure are different when B is reversed. This means that the measured Sₓₓ and Sᵧᵧ have contributions which are both even and odd in B. Sₓₓ is expected to be even under reversal of B and Sᵧᵧ should be odd, but experimentally there is usually some admixture of the one into the other because of imperfect contact alignment. However, in the present experiments such a geometric effect can be excluded as being responsible for the observed behaviour because the unexpected contributions are essentially only seen in the IQH regime and not in the FQH regime, e.g. the odd part of Sₓₓ vanishes for ν < 1 (with some deviation around ν = 3) even though the amplitude of Sₓₓ in the FQH range is rather large.

Another interesting feature is that we find a similar behaviour for the T dependence of Sₓₓ at filling factors of 1/2 and 1/4 as we do with the zero field TEP (see Fig. 2). At ν = 1/2 (1/4), Sₓₓ is about a factor of 20 (50) larger than at zero B. We interpret the measured TEP at ν = 1/2 and 1/4 as the "zero field phonon drag TEP" of the composite Fermions (CF) at these points [8] and deduce that the CFs have a stronger interaction with the phonons than noninteracting electrons. CFs are quasi-particles consisting of an electron bound to an even number of flux quanta [9].

At zero B, the phonon drag TEP Sᵦ, which is usually the main contribution to the TEP [4,5] can be expressed [10,6] as

\[
Sᵦ = -\frac{vLm^*}{eT\tau_{eph}} = -\rho_{ph} nevL, \quad (1)
\]
4. Conclusions

We have measured the TEP of 2DEGs in $B \leq 20$ T and down to 100 mK. At low $T$ we observe field-dependent fluctuations, mainly in the IQH regime, and a diverging TEP around $v = \frac{1}{4}$. The $T$ dependence at $v = \frac{1}{2}$ and $v = \frac{1}{4}$ is found to be similar to the zero field TEP and is interpreted using the composite fermion model. Further experimental as well as theoretical investigations concerning these observations are in progress.

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References